

**DESCRIPTION**

2SA1947 is a resin sealed silicon PNP epitaxial type transistor. It is designed with high collector current and 2 to 3.5W low frequency power amplify. Complementary with 2SC5214.

**FEATURE**

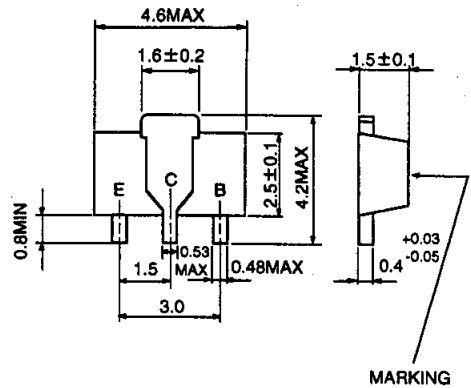
- High  $f_T$   $f_T=100\text{MHz}$  typ
- Excellent linearity of DC forward current gain
- High collector current  $I_{CM}=-1.5\text{A}$
- Small package for mounting

**APPLICATION**

Radio, tape recorder, small type stereo, etc.  
Low frequency power amplify circuit with 2 to 3.5W output.

**OUTLINE DRAWING**

Unit:mm



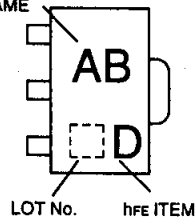
**TERMINAL CONNECTOR**

E : EMITTER  
C : COLLECTOR  
B : BASE  
EIAJ : SC-62  
JEDEC : -

Note)  
The dimension without tolerance represent central value.

**MARKING**

TYPE NAME



**MAXIMUM RATINGS (Ta=25°C)**

Symbol	Parameter	Ratings	Unit
V <sub>CB0</sub>	Collector to Base voltage	-30	V
V <sub>EB0</sub>	Emitter to Base voltage	-4	V
V <sub>CE0</sub>	Collector to Emitter voltage	-25	V
I <sub>CM</sub>	Peak collector current	-1.5	A
I <sub>C</sub>	Collector current	-1	A
P <sub>C</sub>	Collector dissipation(Ta=25°C)	500	mW
T <sub>J</sub>	Junction temperature	+150	°C
T <sub>stg</sub>	Storage temperature	-55 to +150	°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C)**

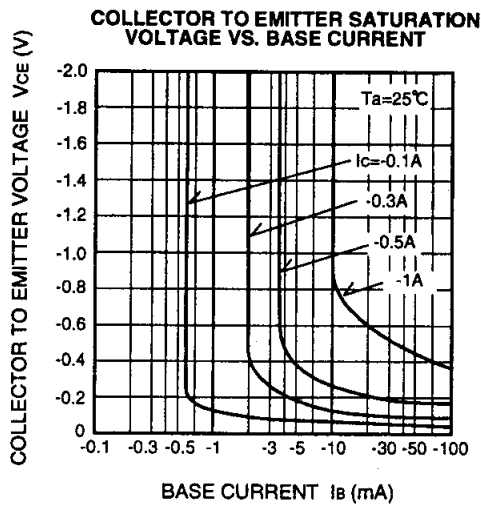
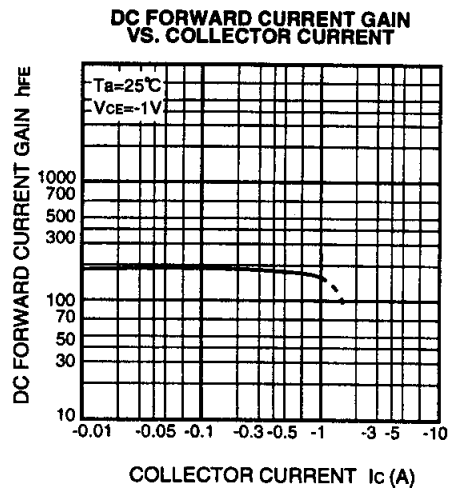
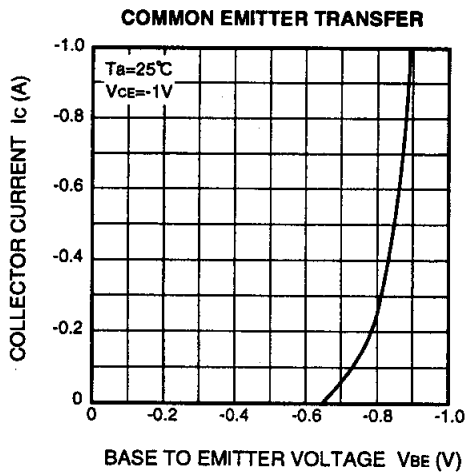
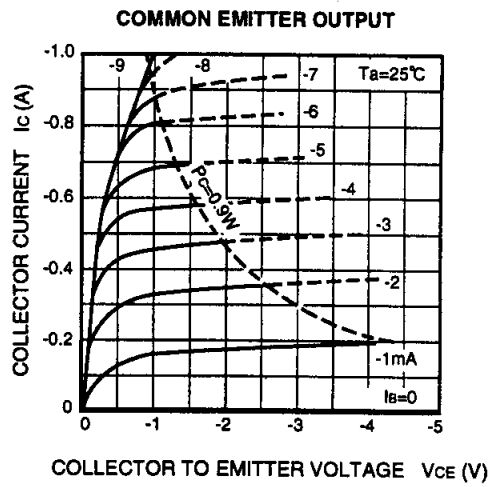
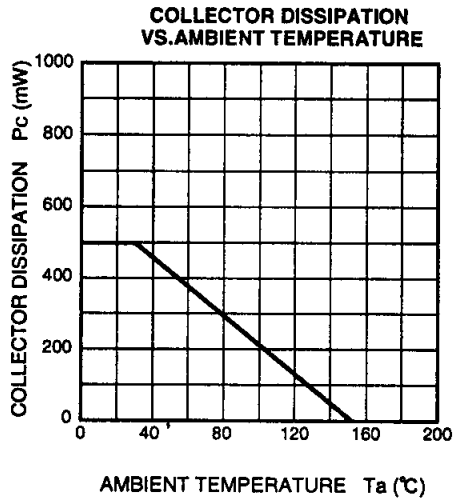
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V <sub>(BR)CBO</sub>	C to B break down voltage	I <sub>C</sub> =-10 μA, I <sub>E</sub> =0	-30			V
V <sub>(BR)EBO</sub>	E to B break down voltage	I <sub>E</sub> =-10 μA, I <sub>C</sub> =0	-4			V
V <sub>(BR)CEO</sub>	C to E break down voltage	I <sub>C</sub> =-100 μA, R <sub>BE</sub> =∞	-25			V
I <sub>CB0</sub>	Collector cut off current	V <sub>CB</sub> =-25V, I <sub>E</sub> =0			-1	μA
I <sub>EB0</sub>	Emitter cut off current	V <sub>BE</sub> =-2V, I <sub>C</sub> =0			-1	μA
h <sub>FE</sub> *	DC forward current gain	V <sub>CE</sub> =-1V, I <sub>C</sub> =-500mA	55		300	—
V <sub>CE(sat)</sub>	C to E saturation voltage	I <sub>C</sub> =-500mA, I <sub>B</sub> =-25mA			-0.5	V
f <sub>T</sub>	Gain band width product	V <sub>CE</sub> =-6V, I <sub>E</sub> =10mA		100		MHz

\* : It shows hFE classification in right table.

Marking	ABC	ABD	ABE
hFE	55 to 110	90 to 180	150 to 300

FOR LOW FREQUENCY POWER AMPLIFY APPLICATION  
SILICON PNP EPITAXIAL TYPE

TYPICAL CHARACTERISTICS



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